

MOSFET

OptiMOS™ Power-Transistor, 60 V

Features

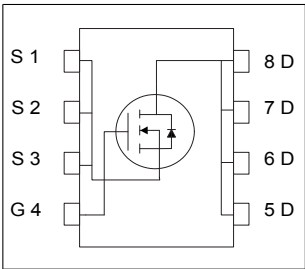
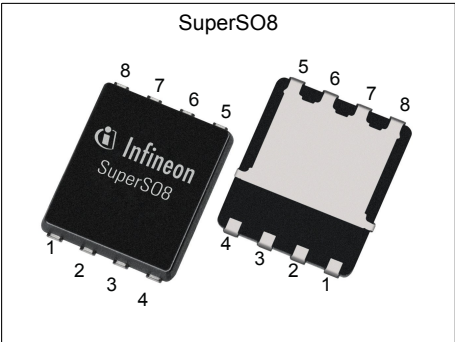
- Ideal for high-frequency switching
- 100% avalanche tested
- Superior thermal resistance
- N-channel, logic level
- Pb-free lead plating; RoHS compliant
- Halogen-free according to IEC61249-2-21
- Optimized for chargers

Product validation

Qualified according to JEDEC Standard

Table 1 Key Performance Parameters

Parameter	Value	Unit
V_{DS}	60	V
$R_{DS(on),max}$	6.5	mΩ
I_D	64	A
Q_{OSS}	19	nC
$Q_G(0V..4.5V)$	10	nC



RoHS

Type / Ordering Code	Package	Marking	Related Links
BSC0703LS	PG-TDSON-8	0703LS	-

Table of Contents

Description 1

Maximum ratings 3

Thermal characteristics 3

Electrical characteristics 4

Electrical characteristics diagrams 6

Package Outlines 10

Revision History 13

Trademarks 13

Disclaimer 13

1 Maximum ratings

at $T_A=25\text{ °C}$, unless otherwise specified

Table 2 Maximum ratings

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Continuous drain current	I_D	-	-	64 41 15	A	$V_{GS}=10\text{ V}$, $T_C=25\text{ °C}$ $V_{GS}=10\text{ V}$, $T_C=100\text{ °C}$ $V_{GS}=10\text{ V}$, $T_A=25\text{ °C}$, $R_{thJA}=50\text{K/W}^{(1)}$
Pulsed drain current ⁽²⁾	$I_{D,pulse}$	-	-	256	A	$T_C=25\text{ °C}$
Avalanche energy, single pulse ⁽³⁾	E_{AS}	-	-	21	mJ	$I_D=40\text{ A}$, $R_{GS}=25\text{ }\Omega$
Gate source voltage	V_{GS}	-20	-	20	V	-
Power dissipation	P_{tot}	-	-	46 2.5	W	$T_C=25\text{ °C}$ $T_A=25\text{ °C}$, $R_{thJA}=50\text{ K/W}^{(1)}$
Operating and storage temperature	T_j , T_{stg}	-55	-	150	°C	IEC climatic category; DIN IEC 68-1: 55/150/56

2 Thermal characteristics

Table 3 Thermal characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Thermal resistance, junction - case, bottom	R_{thJC}	-	1.6	2.7	K/W	-
Device on PCB, 6 cm ² cooling area ⁽¹⁾	R_{thJA}	-	-	50	K/W	-

⁽¹⁾ Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm² (one layer, 70 µm thick) copper area for drain connection. PCB is vertical in still air.

⁽²⁾ See Diagram 3 for more detailed information

⁽³⁾ See Diagram 13 for more detailed information

3 Electrical characteristics

at $T_j=25\text{ °C}$, unless otherwise specified

Table 4 Static characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Drain-source breakdown voltage	$V_{(BR)DSS}$	60	-	-	V	$V_{GS}=0\text{ V}$, $I_D=1\text{ mA}$
Gate threshold voltage	$V_{GS(th)}$	1.1	1.7	2.3	V	$V_{DS}=V_{GS}$, $I_D=20\text{ }\mu\text{A}$
Zero gate voltage drain current	I_{DSS}	-	0.1 10	1 100	μA	$V_{DS}=60\text{ V}$, $V_{GS}=0\text{ V}$, $T_j=25\text{ °C}$ $V_{DS}=60\text{ V}$, $V_{GS}=0\text{ V}$, $T_j=125\text{ °C}$
Gate-source leakage current	I_{GSS}	-	10	100	nA	$V_{GS}=20\text{ V}$, $V_{DS}=0\text{ V}$
Drain-source on-state resistance	$R_{DS(on)}$	-	5.3 7.2	6.5 9.2	m Ω	$V_{GS}=10\text{ V}$, $I_D=32\text{ A}$ $V_{GS}=4.5\text{ V}$, $I_D=16\text{ A}$
Gate resistance ¹⁾	R_G	-	1.2	1.8	Ω	-
Transconductance	g_{fs}	32	63	-	S	$ V_{DS} >2 I_D R_{DS(on)max}$, $I_D=32\text{ A}$

Table 5 Dynamic characteristics¹⁾

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Input capacitance	C_{iss}	-	1400	1800	pF	$V_{GS}=0\text{ V}$, $V_{DS}=30\text{ V}$, $f=1\text{ MHz}$
Output capacitance	C_{oss}	-	300	390	pF	$V_{GS}=0\text{ V}$, $V_{DS}=30\text{ V}$, $f=1\text{ MHz}$
Reverse transfer capacitance	C_{rss}	-	16	28	pF	$V_{GS}=0\text{ V}$, $V_{DS}=30\text{ V}$, $f=1\text{ MHz}$
Turn-on delay time	$t_{d(on)}$	-	5	-	ns	$V_{DD}=30\text{ V}$, $V_{GS}=10\text{ V}$, $I_D=32\text{ A}$, $R_{G,ext}=3\text{ }\Omega$
Rise time	t_r	-	3	-	ns	$V_{DD}=30\text{ V}$, $V_{GS}=10\text{ V}$, $I_D=32\text{ A}$, $R_{G,ext}=3\text{ }\Omega$
Turn-off delay time	$t_{d(off)}$	-	14	-	ns	$V_{DD}=30\text{ V}$, $V_{GS}=10\text{ V}$, $I_D=32\text{ A}$, $R_{G,ext}=3\text{ }\Omega$
Fall time	t_f	-	3	-	ns	$V_{DD}=30\text{ V}$, $V_{GS}=10\text{ V}$, $I_D=32\text{ A}$, $R_{G,ext}=3\text{ }\Omega$

Table 6 Gate charge characteristics²⁾

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Gate to source charge	Q_{gs}	-	4.4	-	nC	$V_{DD}=30\text{ V}$, $I_D=32\text{ A}$, $V_{GS}=0\text{ to }4.5\text{ V}$
Gate charge at threshold	$Q_{g(th)}$	-	2.4	-	nC	$V_{DD}=30\text{ V}$, $I_D=32\text{ A}$, $V_{GS}=0\text{ to }4.5\text{ V}$
Gate to drain charge ¹⁾	Q_{gd}	-	3.3	5	nC	$V_{DD}=30\text{ V}$, $I_D=32\text{ A}$, $V_{GS}=0\text{ to }4.5\text{ V}$
Switching charge	Q_{sw}	-	5.3	-	nC	$V_{DD}=30\text{ V}$, $I_D=32\text{ A}$, $V_{GS}=0\text{ to }4.5\text{ V}$
Gate charge total ¹⁾	Q_g	-	10	13	nC	$V_{DD}=30\text{ V}$, $I_D=32\text{ A}$, $V_{GS}=0\text{ to }4.5\text{ V}$
Gate plateau voltage	$V_{plateau}$	-	3.1	-	V	$V_{DD}=30\text{ V}$, $I_D=32\text{ A}$, $V_{GS}=0\text{ to }4.5\text{ V}$
Gate charge total, sync. FET	$Q_{g(sync)}$	-	18	-	nC	$V_{DS}=0.1\text{ V}$, $V_{GS}=0\text{ to }10\text{ V}$
Output charge ¹⁾	Q_{oss}	-	19	25.5	nC	$V_{DD}=30\text{ V}$, $V_{GS}=0\text{ V}$

¹⁾ Defined by design. Not subject to production test

²⁾ See "Gate charge waveforms" for parameter definition

Table 7 Reverse diode

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Diode continuous forward current	I_S	-	-	39	A	$T_C=25\text{ °C}$
Diode pulse current	$I_{S,pulse}$	-	-	156	A	$T_C=25\text{ °C}$
Diode forward voltage	V_{SD}	-	0.9	1.2	V	$V_{GS}=0\text{ V}$, $I_F=32\text{ A}$, $T_j=25\text{ °C}$
Reverse recovery time ¹⁾	t_{rr}	-	24	48	ns	$V_R=30\text{ V}$, $I_F=32$, $di_F/dt=100\text{ A/}\mu\text{s}$
Reverse recovery charge ¹⁾	Q_{rr}	-	14	28	nC	$V_R=30\text{ V}$, $I_F=32$, $di_F/dt=100\text{ A/}\mu\text{s}$

¹⁾ Defined by design. Not subject to production test

4 Electrical characteristics diagrams

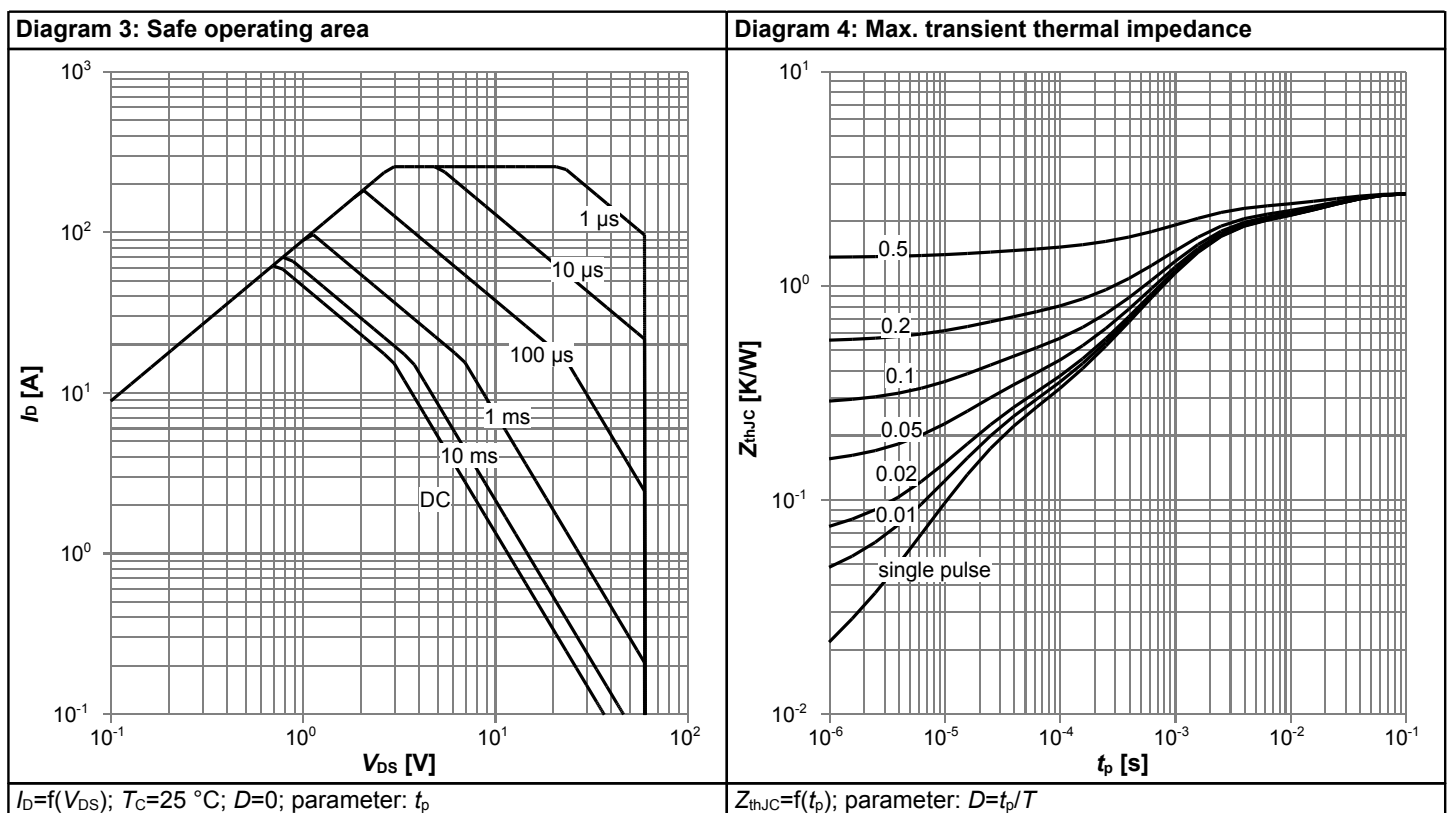
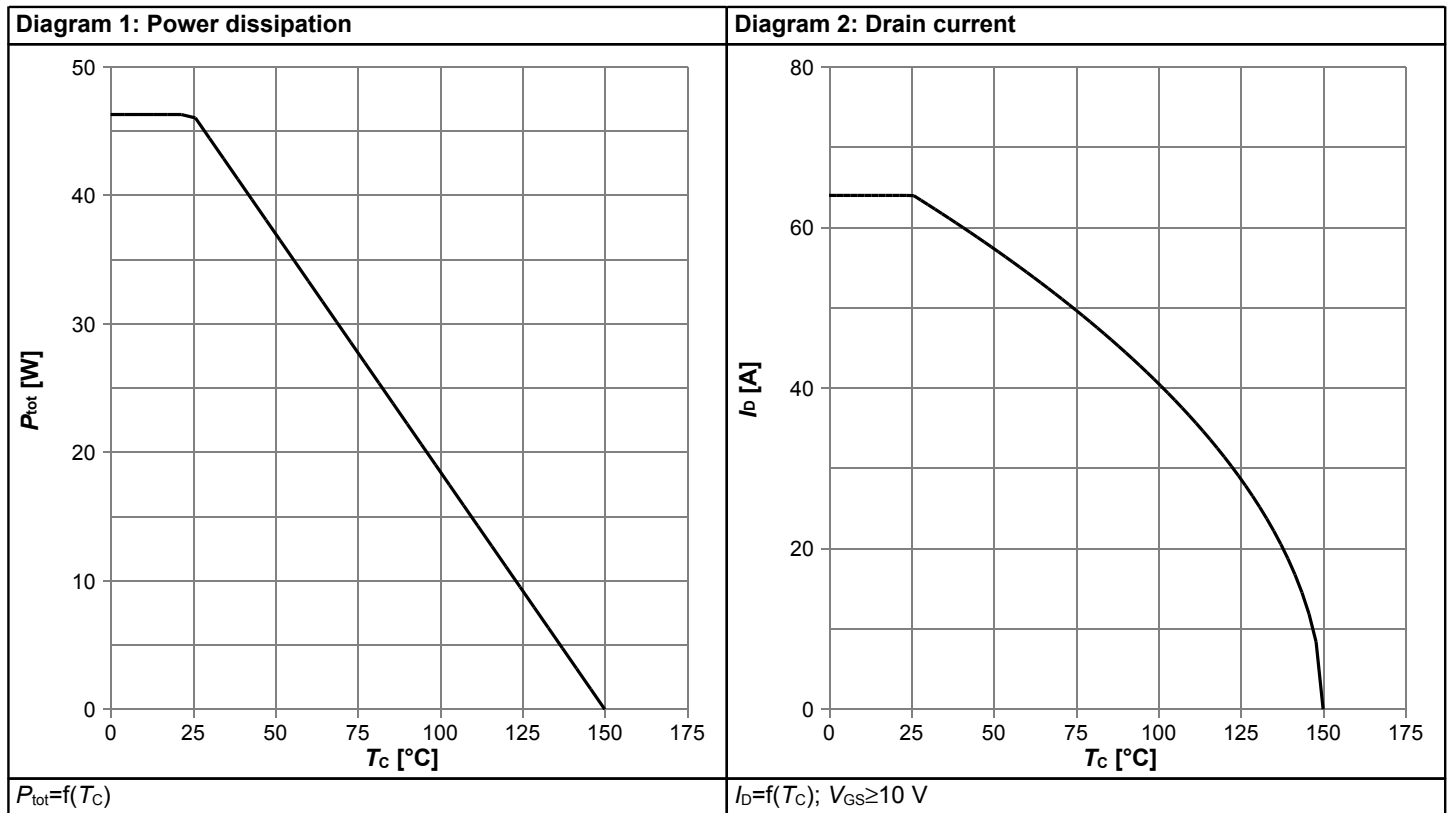
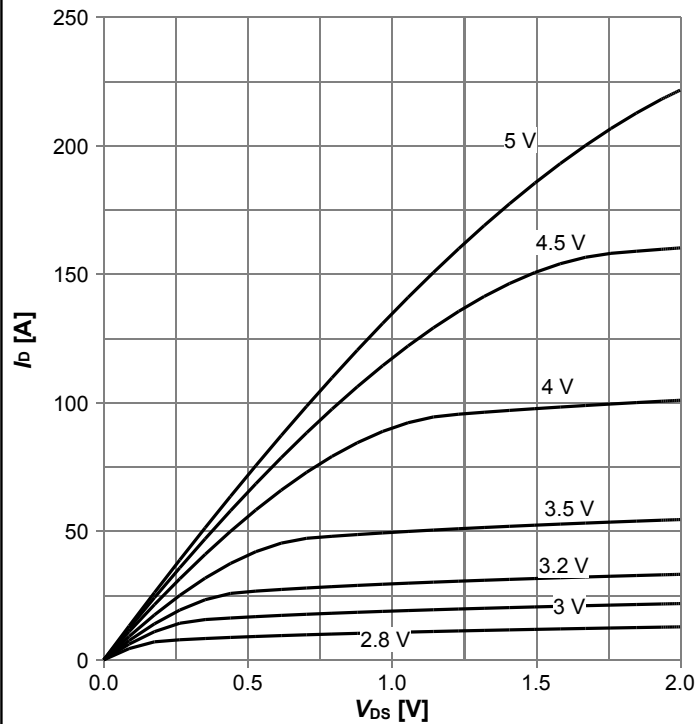
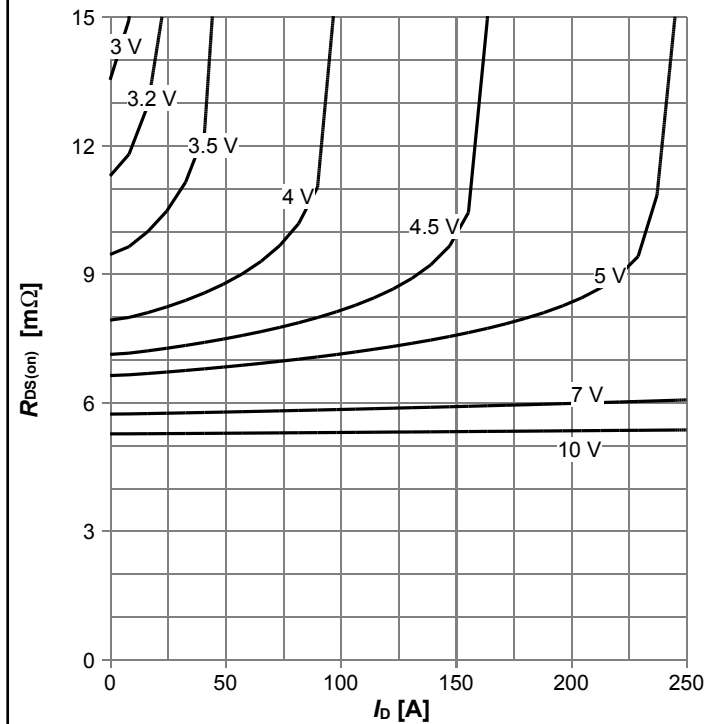


Diagram 5: Typ. output characteristics



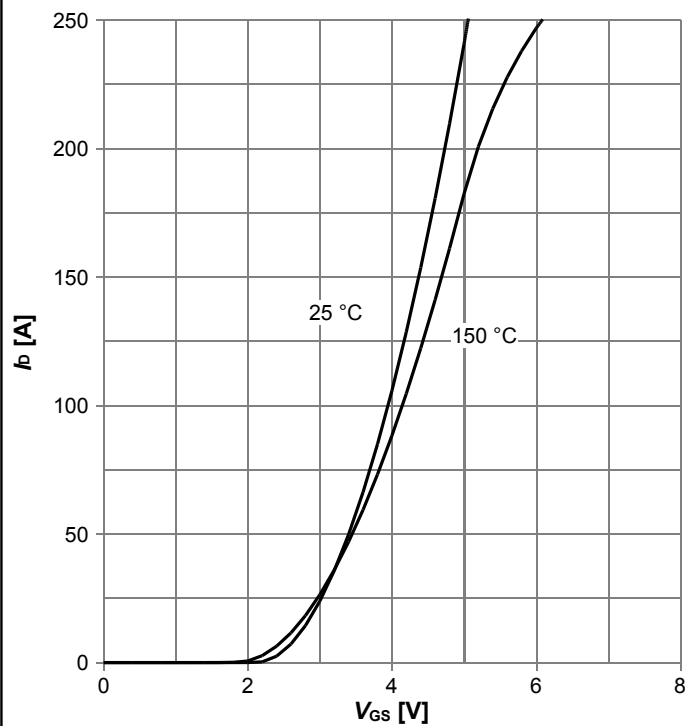
$I_D = f(V_{DS})$; $T_j = 25^\circ\text{C}$; parameter: V_{GS}

Diagram 6: Typ. drain-source on resistance



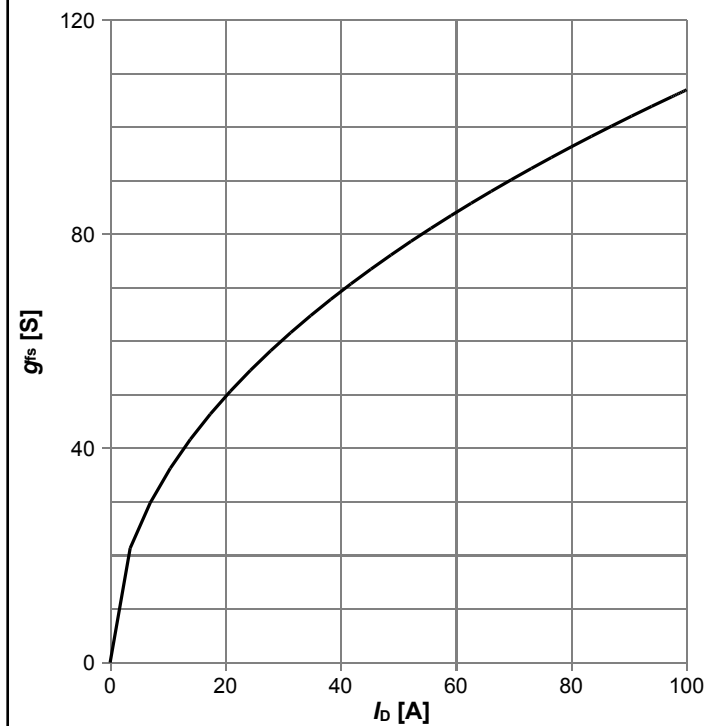
$R_{DS(on)} = f(I_D)$; $T_j = 25^\circ\text{C}$; parameter: V_{GS}

Diagram 7: Typ. transfer characteristics



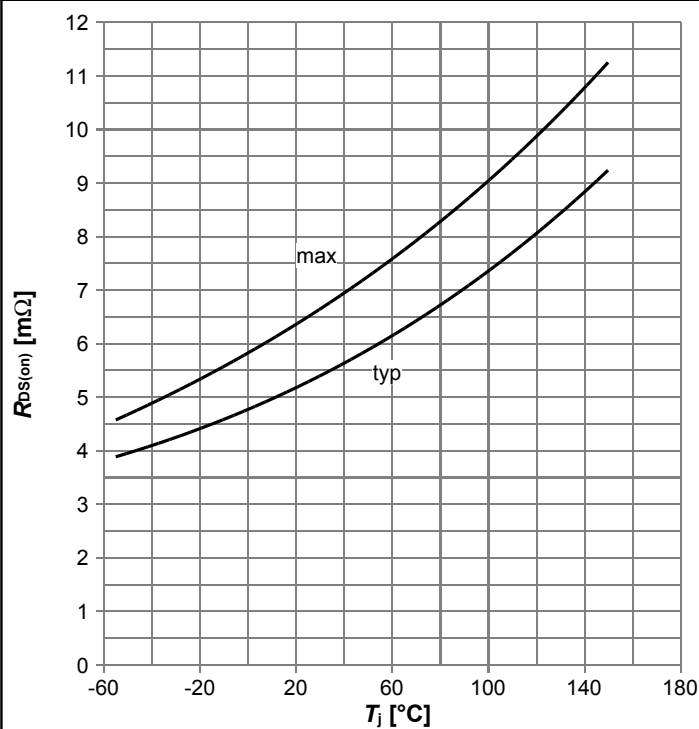
$I_D = f(V_{GS})$; $|V_{DS}| > 2|I_D|R_{DS(on)max}$; parameter: T_j

Diagram 8: Typ. forward transconductance



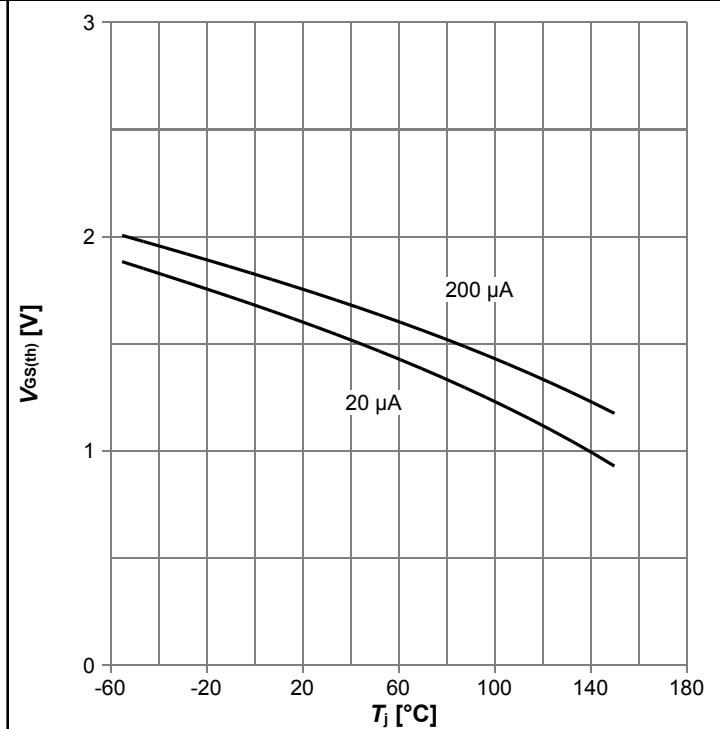
$g_{fs} = f(I_D)$; $T_j = 25^\circ\text{C}$

Diagram 9: Drain-source on-state resistance



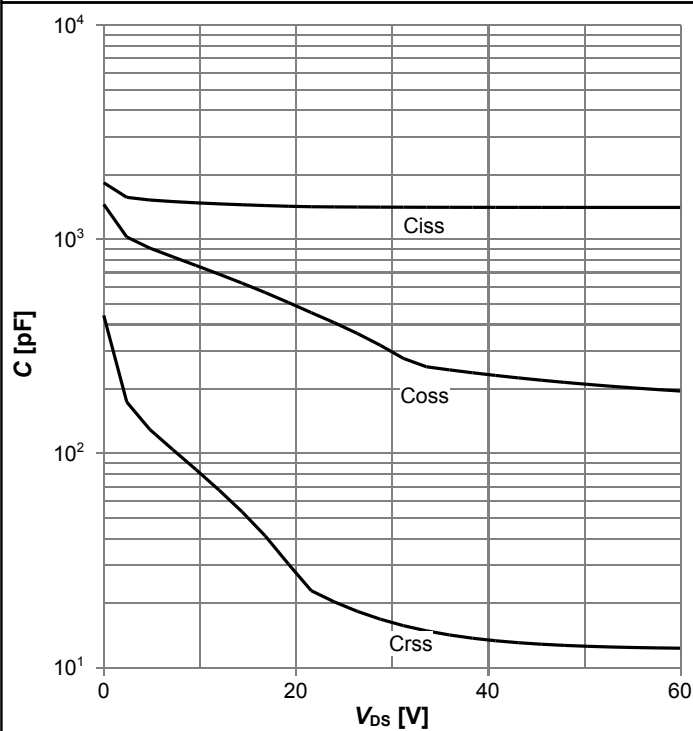
$R_{DS(on)} = f(T_j)$; $I_D = 32$ A; $V_{GS} = 10$ V

Diagram 10: Typ. gate threshold voltage



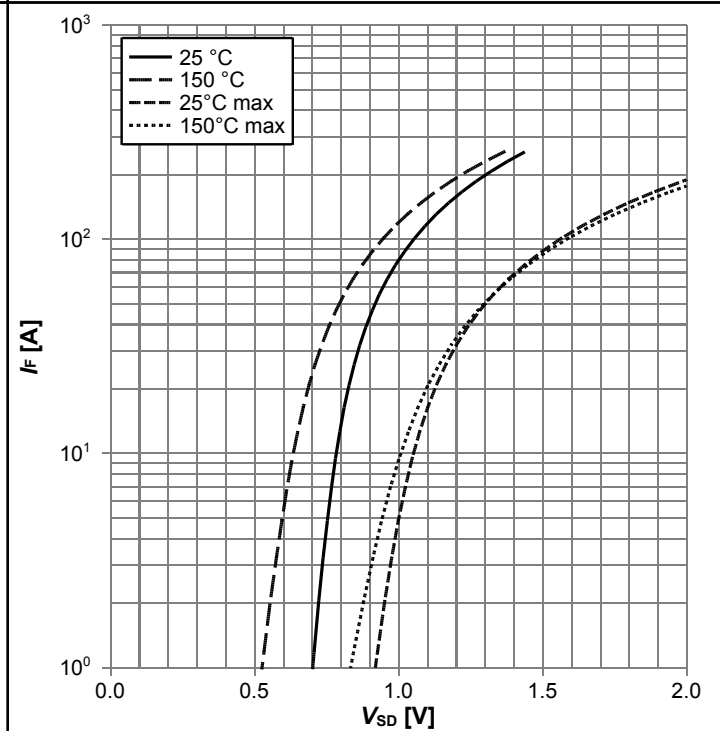
$V_{GS(th)} = f(T_j)$; $V_{GS} = V_{DS}$

Diagram 11: Typ. capacitances



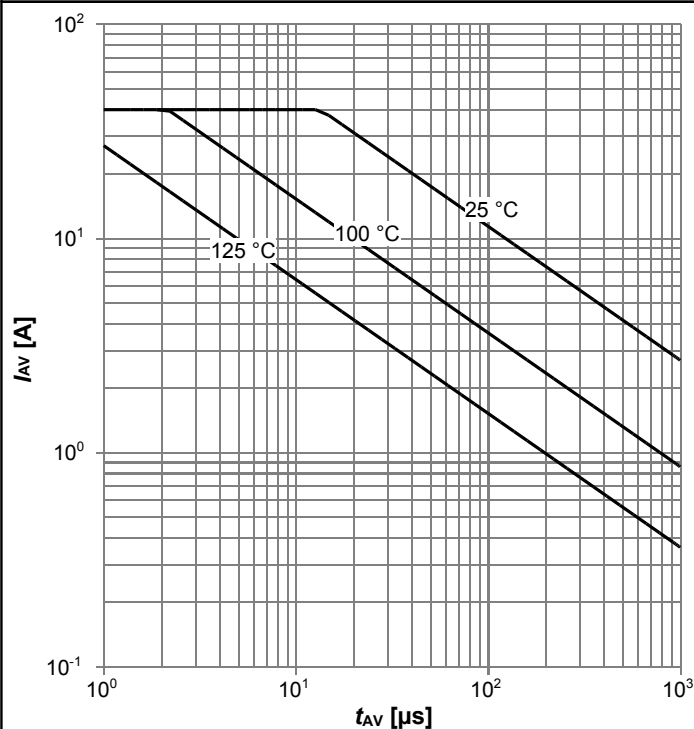
$C = f(V_{DS})$; $V_{GS} = 0$ V; $f = 1$ MHz

Diagram 12: Forward characteristics of reverse diode



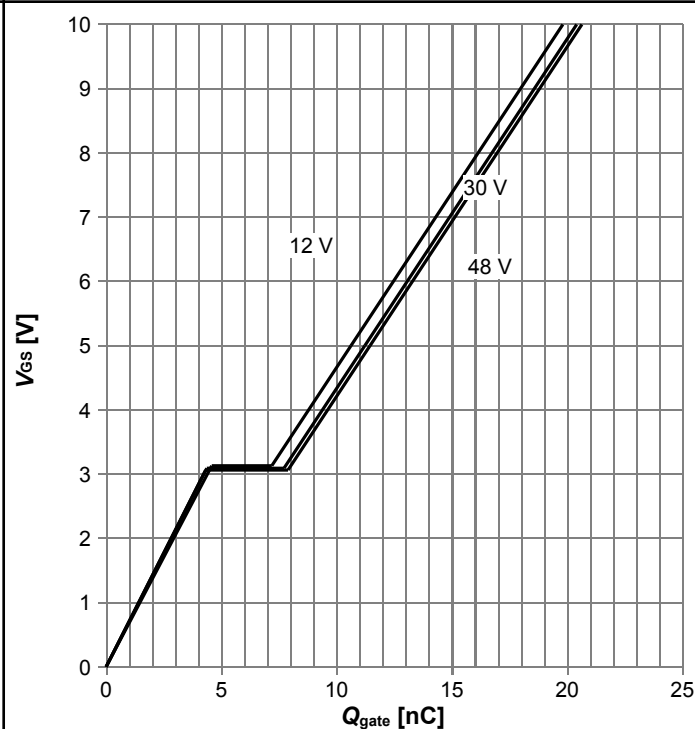
$I_F = f(V_{SD})$; parameter: T_j

Diagram 13: Avalanche characteristics



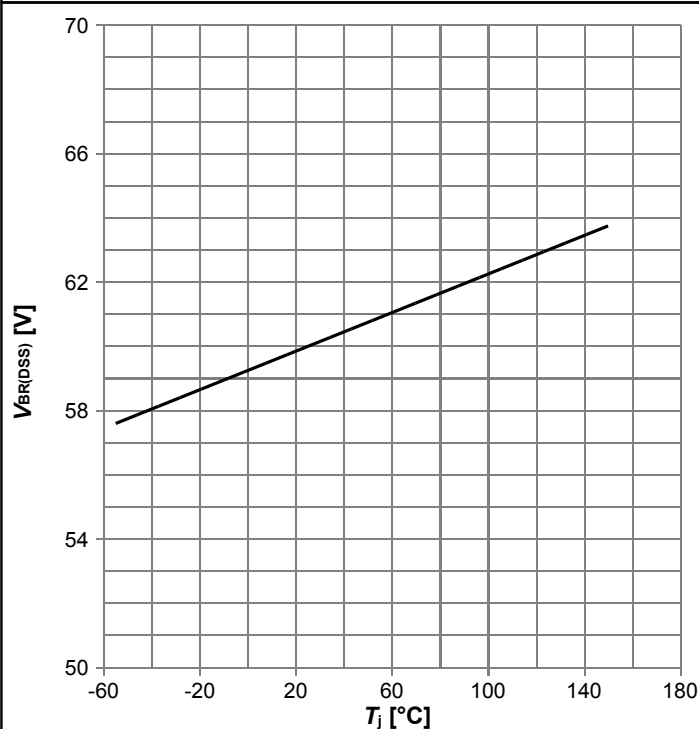
$I_{AS}=f(t_{AV})$; $R_{GS}=25\ \Omega$; parameter: $T_{j(start)}$

Diagram 14: Typ. gate charge



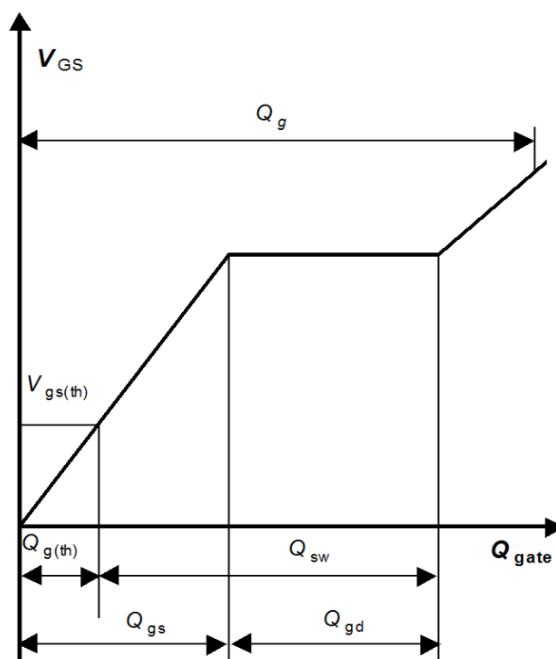
$V_{GS}=f(Q_{gate})$; $I_D=32\text{ A}$ pulsed; parameter: V_{DD}

Diagram 15: Drain-source breakdown voltage



$V_{BR(DSS)}=f(T_J)$; $I_D=1\text{ mA}$

Diagram Gate charge waveforms



5 Package Outlines



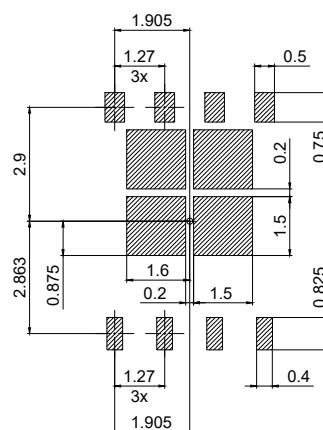
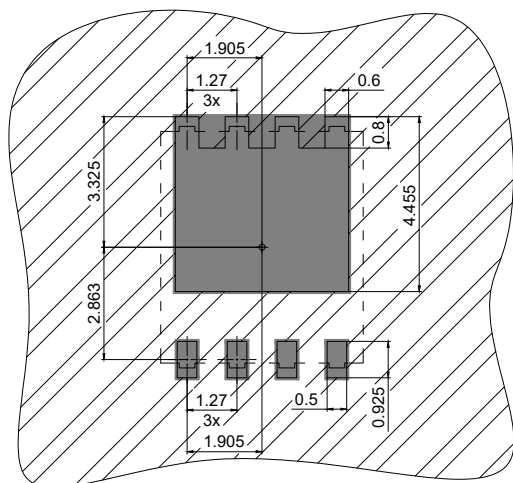
- 1) EXCLUDING MOLD FLASH
2) REMOVAL ON MOLD GATE
INTRUSION 0.1 MM
PROTRUSION 0.1 MM
LEAD LENGTH UP TO ANTI FLASH LINE
ALL METAL SURFACES ARE PLATED, EXCEPT AREA OF CUT

DIMENSION	MILLIMETERS	
	MIN.	MAX.
A	0.90	1.20
A1	0.15	0.35
b	0.34	0.54
D	4.80	5.35
D1	3.90	4.40
D2	0.03	0.23
E	5.70	6.10
E1	5.90	6.42
E2	3.88	4.31
e	1.27	
L	0.45	0.71
M	0.45	0.69

DOCUMENT NO. Z8B00003332
REVISION 07
SCALE 10:1 0 1 2 3mm
EUROPEAN PROJECTION
ISSUE DATE 06.06.2019

Figure 1 Outline PG-TDSON-8, dimensions in mm

PG-TDSON-8: Recommended Boardpads & Apertures



■ copper

▨ solder mask

▨ stencil apertures

all dimensions in mm

Figure 2 Outline Boardpads (TDSON-8), dimensions in mm



Rev. 2.2, 2020-05-15

Revision History

BSC0703LS

Revision: 2020-05-15, Rev. 2.2

Previous Revision

Revision	Date	Subjects (major changes since last revision)
2.0	2016-10-06	Release of final version
2.1	2016-10-20	Update " Features "
2.2	2020-05-15	Update package drawings

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